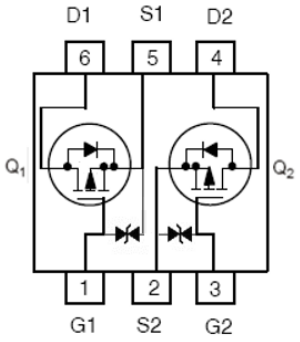
P-Channel Enhancement Mode MOSFET

TBSS7001-6L

Features

HF

- Low on-resistance
- High-speed switching
- Drive circuits can be simple
- Parallel use is easy
- HBM: AEC-Q101-001: H2 (JESD22-A114-B: 2)
- RoHS compliant with Halogen-free
- Qualified to AEC-Q101 Standards

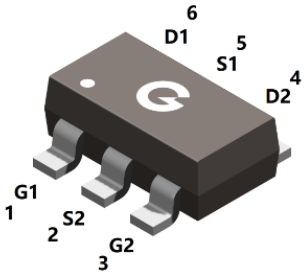


Typical Applications

- P-channel enhancement mode effect transistor
- Switching application

Mechanical Data

- Case: SOT-23-6L
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



SOT-23-6L

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
TBSS7001-6L	SOT-23-6L	3000 pcs / Tape & Reel	7001

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-60	V
Gate -Source Voltage	V_{GSS}	±20	V
Continuous Drain Current (T_A = 25°C) *1	I_D	-0.35	A
Continuous Drain Current (T_A = 70°C) *1		-0.28	A
Pulsed Drain Current (t_p = 10μs, T_A = 25°C)	I_{DM}	-1.4	A
Single Pulse Avalanche Energy *3	E_{AS}	0.3	mJ
Power Dissipation (T_A = 25°C) *1	P_D	1	W
Operating Junction Temperature Range	T_J	-55 ~ +150	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	65	70	°C/W
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	-	110	125	°C/W

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = -250μA	-60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -60V, V_{GS} = 0V	-	-	-1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±10	μA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance *2	V_{GS} = -10V, I_D = -0.1A	-	1.8	4	Ω
		V_{GS} = -4.5V, I_D = -0.1A	-	2.3	5	
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250μA	-1	-1.5	-2	V
Dynamic Characteristics						
g_{fs}	Transconductance	V_{DS} = -10V, I_D = -0.2A	-	0.5	-	S
C_{ISS}	Input Capacitance	V_{GS} = 0V V_{DS} = -20V f = 1.0MHz	-	39	-	pF
C_{OSS}	Output Capacitance		-	12	-	
C_{RSS}	Reverse Transfer Capacitance		-	2	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time *4	V_{DS} = -15V R_L = -50Ω I_D = -2.5A	-	2.5	-	ns
t_r	Turn-on Rise Time *4		-	1	-	
$t_{d(OFF)}$	Turn-Off Delay Time *4		-	16	-	
t_f	Turn-Off Fall Time *4		-	8	-	
Q_G	Total Gate-Charge	V_{DS} = -25V V_{GS} = -4.5V I_D = -0.2A	-	2	-	nC
Q_{GS}	Gate to Source Charge		-	0.7	-	
Q_{GD}	Gate to Drain (Miller) Charge		-	0.5	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage *2	I_S = -0.2A, V_{GS} = 0 V	-	-0.87	-1.4	V

Notes:

1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
3. The E_{AS} data shows Max. rating. The test condition is V_{DD} = -30V, V_{GS} = -10V, L = 0.1mH
4. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)

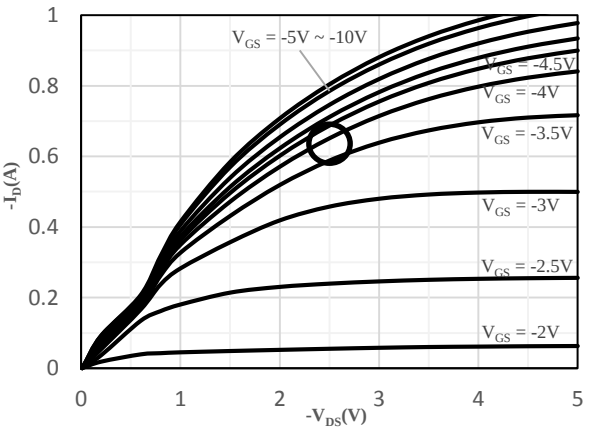


Fig 1 Typical Output Characteristics

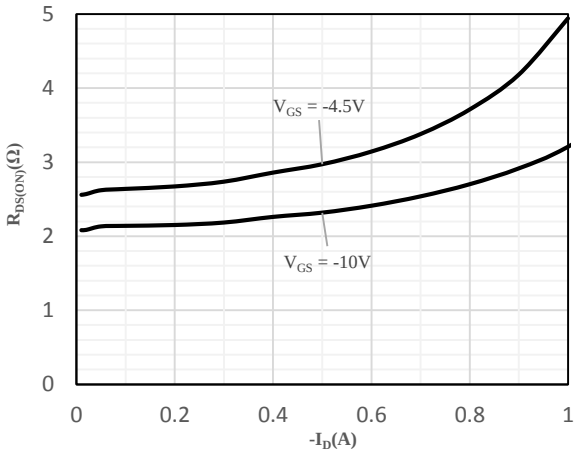


Fig 2 On-Resistance vs. Drain Current and Gate Voltage

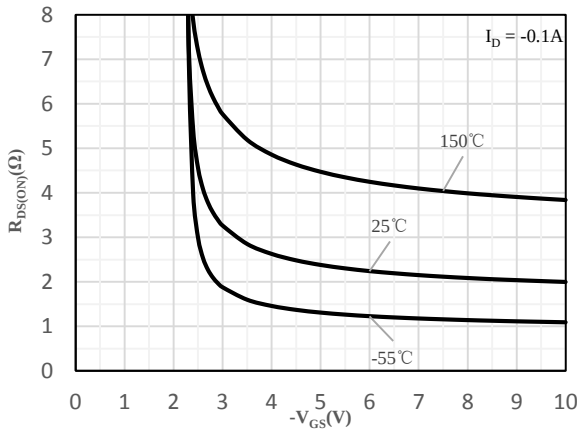


Fig 3 On-Resistance vs. Gate-Source Voltage

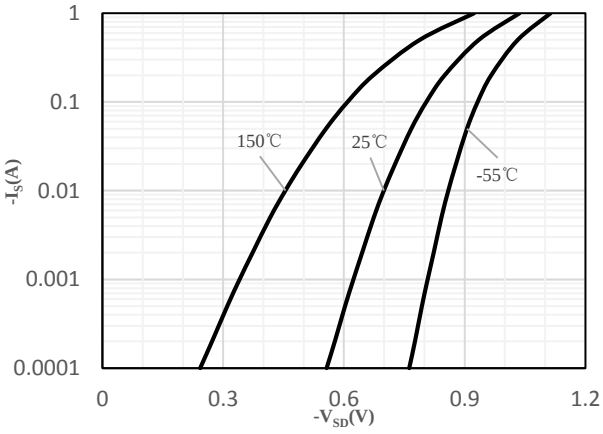


Fig 4 Body-Diode Characteristics

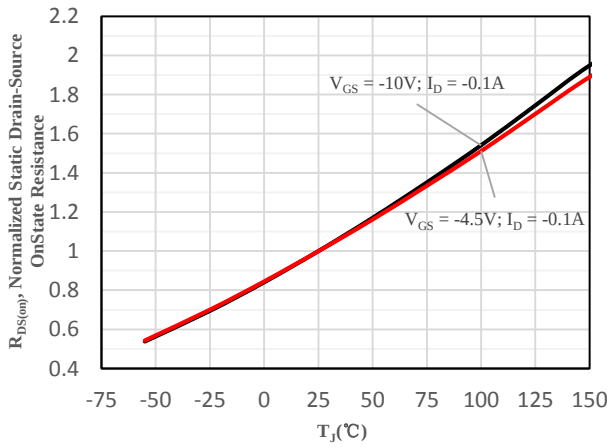


Fig 5 Normalized On-Resistance vs. Junction Temperature

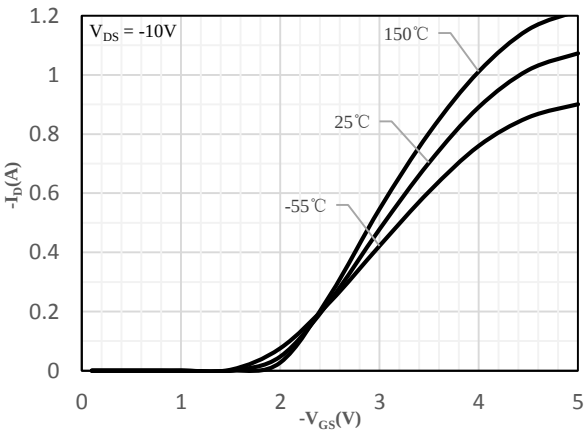


Fig 6 Transfer Characteristics

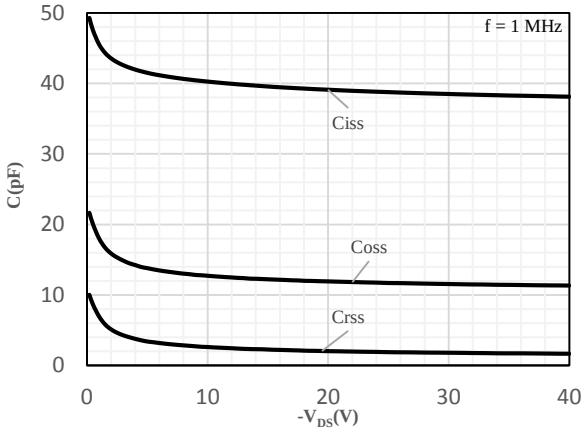


Fig 7 Capacitance Characteristics

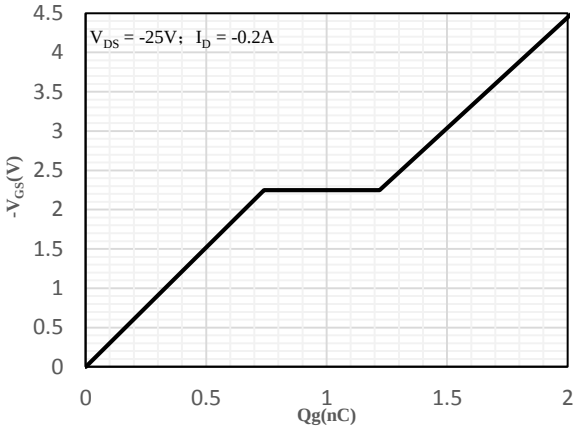


Fig 8 Gate-Charge Characteristics

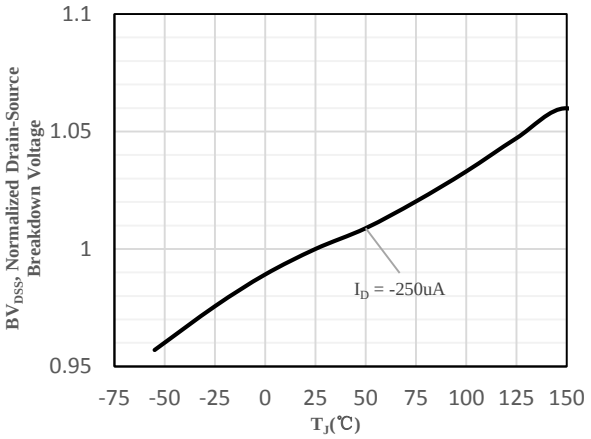


Fig 9 Normalized Breakdown Voltage vs. Junction Temperature

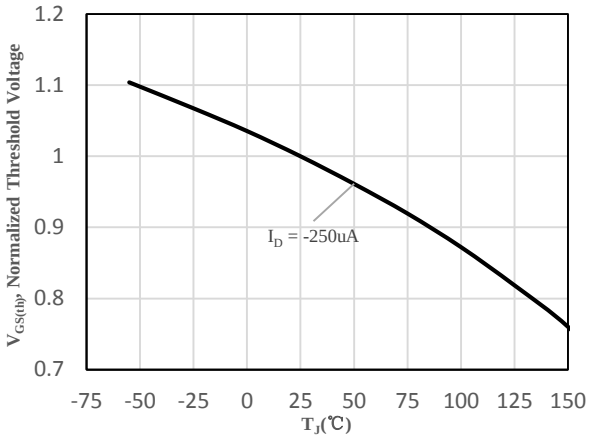


Fig 10 Normalized $V_{GS(th)}$ vs. Junction Temperature

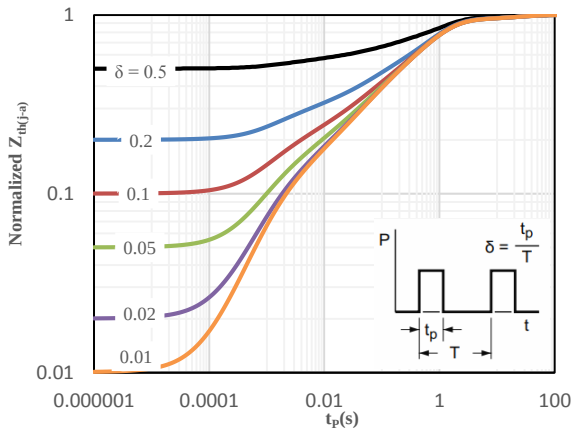
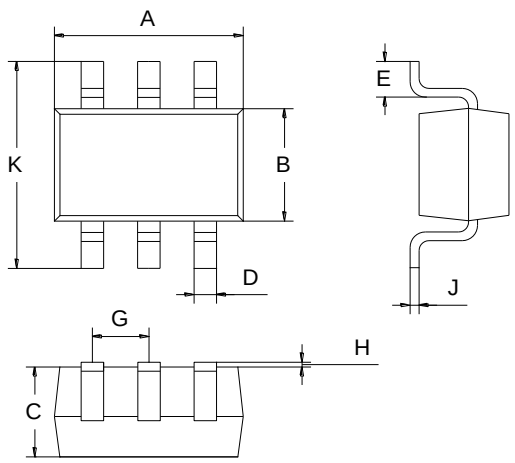


Fig 11 Normalized Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



SOT-23-6L		
Dimension	**Min.**	**Max.**
A	2.80	3.00
B	1.50	1.70
C	1.00	1.20
D	0.35	0.45
E	0.35	0.55
G	0.90	1.00
H	0.02	0.10
J	0.10	0.20
K	2.60	3.00

Mounting Pad Layout (Unit: mm)

SOT-23-6L